



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C	
60V	$6\Omega @ V_{GS} = 5V$	200mA	

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- ESD Protected Gate, 1.2kV HBM
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- The 2N7002AQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

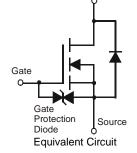
- Motor Control
- **Power Management Functions**

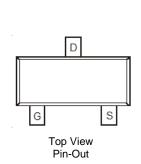
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Alloy 42 Lead-Frame. Solderable per MIL-STD-202, Method 208 @3
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)

Drain







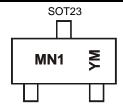
Ordering Information (Note 4)

Part Number	Case	Packaging
2N7002AQ-7	SOT23	3,000/Tape & Reel
2N7002AQ-13	SOT23	10,000/Tape & Reel

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. Notes:

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain < 900ppm bromine, < 900ppm chlorine (< 1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



MN1 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2015	•••	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	С		Н	-	J	K	L	М	N	0	Р	R
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code		_	_		_		_	_	_)

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Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		V_{DSS}	60	V	
Gate-Source Voltage		V_{GSS}	±20	V	
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State	$T_A = +25$ °C $T_A = +85$ °C $T_A = +100$ °C	l _D	180 130 115	mA
Continuous Drain Current (Note 6) $V_{GS} = 10V$ Steady $T_A = +25^{\circ}C$ $T_A = +85^{\circ}C$ $T_A = +100^{\circ}C$		l _D	220 160 140	mA	
Maximum Continuous Body Diode Forward Current	(Note 6)	Is	220	mA	
Pulsed Drain Current (10µs pulse, duty cycle = 1%))		I _{DM}	800	mA

Thermal Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Total Power Dissipation	(Note 5)	D	370	mW	
Total Power Dissipation	(Note 6)	P _D	540	IIIVV	
Thermal Resistance, Junction to Ambient	(Note 5)	ב	348		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	241	°C/W	
Thermal Resistance, Junction to Case	(Note 6)	R _{θJC}	91		
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C	

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)							•
Drain-Source Breakdown Voltage		BV _{DSS}	60	70	_	V	$V_{GS} = 0V, I_{D} = 10\mu A$
Zero Gate Voltage Drain Current @ $T_C = +25^{\circ}C$ @ $T_C = +125^{\circ}C$		I _{DSS}	_	_	1.0 500	μΑ	V _{DS} = 60V, V _{GS} = 0V
Gate-Body Leakage	ate-Body Leakage		_	_	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage		V _{GS(th)}	1.2	_	2.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
Static Drain-Source On-Resistance	tic Drain-Source On-Resistance @ T _J = +25°C		Б	3.5 6	6	Ω	V _{GS} = 5.0V, I _D = 0.115A
	@ T _J = +125°C	R _{DS(ON)}	CDS(ON) - 3.0	5	V _{GS} = 10V, I _D = 0.115A		
Forward Transconductance	Forward Transconductance		80	_	_	mS	V _{DS} = 10V, I _D = 0.115A
DYNAMIC CHARACTERISTICS (Note	8)						
Input Capacitance		C _{iss}	_	23	_	pF	
Output Capacitance		Coss	_	3.4	—	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Reverse Transfer Capacitance		Crss	_	1.4	_	pF]
Gate Resistance		R_{G}	_	260	400	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
SWITCHING CHARACTERISTICS (No	ote 8)				•		
Turn-On Delay Time		t _{D(ON)}		10	_	ns	$V_{DD} = 30V, I_D = 0.115A, R_L = 150$
Turn-Off Delay Time		t _{D(OFF)}	_	33	_	ns	Ω , V _{GEN} = 10V, R _{GEN} = 25 Ω

Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.

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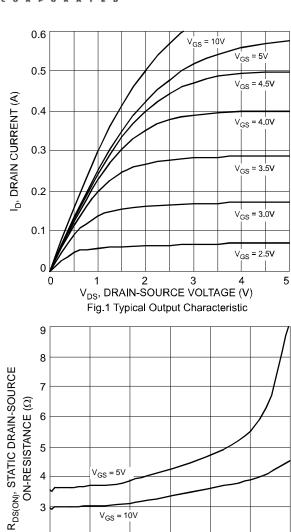


Fig. 3 On-Resistance vs. Drain Current & Gate Voltage

0.3

 I_D , DRAIN-SOURCE CURRENT (A)

0.4

0.5

 $V_{GS} = 5V$

 $V_{GS} = 10V$

0.2

3

2

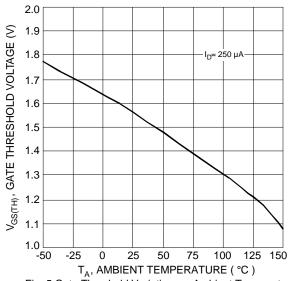
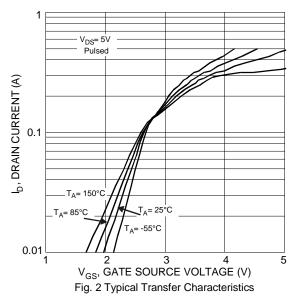


Fig. 5 Gate Threshold Variation vs. Ambient Temperature



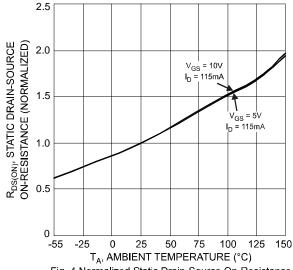
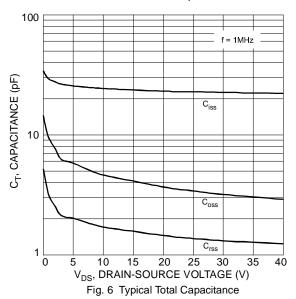


Fig. 4 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature





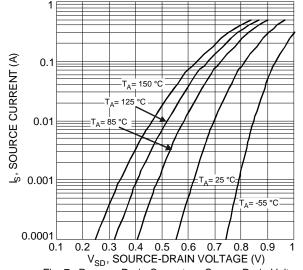
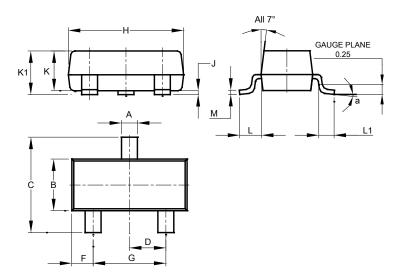


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

Package Outline Dimensions

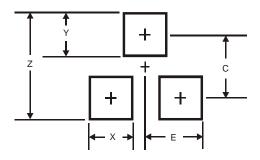
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
а		8°						
All	Dimens	ions in	mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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